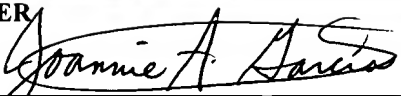


Form PTO-1449 U.S. DEPARTMENT OF COMMERCE (REV. 8-83) PATENT AND TRADEMARK OFFICE				ATTY. DOCKET NO. BU9-98-179		SERIAL NO. 09/224,759		
INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				APPLICANT Furukawa et al.				
				FILING DATE 1-4-99		GROUP 2823		
U. S. PATENT DOCUMENTS								
EXAMINE R INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE	
FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION	
							YES	NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)								
JAS		Stanoslovich, et al. "Method for Reducing the Diffusion Contact Borders", IBM Technical Disclosure Bulletin, Vol. 32, No. 4A, September 1989, pgs. 344-345.						
JAS		Weiner et al. "Self Aligned Silicide Formation Using Gas Immersion Laser Annealing (GILA)", Ultratech Stepper technical brief, March 3, 1997.						
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JAS		Derwent World Patent Index "Japanese Patent 8148680 Abstract", June 7, 1996.						
EXAMINER				DATE CONSIDERED				
Joanne A. Sarna				June 2, 2001				
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JAG		5,668,065	09/1997	Lin	—	—		
JAG		5,620,912	04/1997	Hwang et al.	—	—		
JAG		5,397,722	03/1995	Bashir et al.	—	—		
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FOREIGN PATENT DOCUMENTS								
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							YES	NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)								
JAG		Jasinski et al. 27341 "Photochemical Deposition of Graded Silicon Nitride", Research Disclosure, January 1987, Number 273						
		Jasinski et al. 27343 "Photochemical Deposition of Silicon Nitride", Research Disclosure, January 1987, Number 273						
JAG		Mihailescu et al. "Direct nitridation of a silicon surface by multipulse excimer laser irradiation in a nitrogen-containing ambient gas", Journal of Applied Physics 70, August 15, 1991, pp 2123-2131.						
JAG		Mihailescu et al. "Synthesis and deposition of silicon nitride films by laser reactive ablation of silicon in low pressure ammonia: A parametric study", Journal of Vacuum Science Technology 14, July/August 1996, pp 1986-1994.						
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